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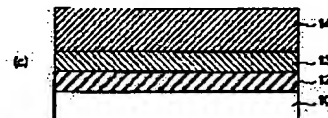
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(54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PROBLEM TO BE SOLVED: To improve a reliability of a gate insulating film made of metallic oxide to improve element characteristics and reliability.

SOLUTION: The method for manufacturing a semiconductor device using a metallic oxide film for a gate insulating film or the like includes steps of forming a TiN film 11 on a silicon substrate 10 by a CVD process and subjecting the resultant laminate to a heat treatment to oxidize the film 11 in an O₂ atmosphere into a TiO₂ film 12, forming a TiN film 13 as a barrier metal on the TiO₂ film 12, and then forming a gate electrode 14 on the TiN film 13.



LEGAL STATUS

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